Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	62675	SiC silicon adj carbide and colloidial adj silica	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/17 13:32
S2	1	silicon adj carbide and colloidial adj silica	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 17:53
S3	0	cmp and colloidial adj silica	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 17:53
S4	1	Polishing and colloidial adj silica	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 17:54
S5	22	colloidial adj silica	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 18:01
S6	2304	polishing same silicon adj carbide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 18:01
S7	963	polishing same silicon adj carbide and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 18:23

S8	94	("5964942" "5989755" "6140210" "6328796" "6497763" "5635269" "5676723" "6127068" "6248395" "6534228" "6150023" "5584898" "5670253" "5913974" "6284628" "6322427" "6362076" "6596610" "6720640" "5686364" "6261928" "6120353" "5582897" "5591502" "5705421" "5705423" "5744401" "5855998" "5981392" "6004866" "6117750" "6193585" "5352277" "5438951" "5500607" "5543648" "5571373" "5733177" "5736226" "5767691" "5776246" "5869387" "5874130" "6008128" "6051063" "6121117" "6171982" "6189546" "6230720" "6238272").pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 18:23
S9	272	polishing same silicon adj carbide same semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/08 10:46
S10	204	angled ion implantation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/07 19:08
S11	6	gate shadowing	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/02/07 19:08
S12	47	polishing same silicon adj carbide adj substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/08 12:59
S13	19	polishing same silicon adj carbide adj substrate and diamond	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/08 11:30
S14	6	polishing same silicon adj carbide adj substrate and silica	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/08 10:49
S15	2	("5895583").PN.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/08 11:30

S16	1	polishing same silicon adj carbide adj substrate and oxidizing adj atmosphere	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/08 13:10
S17	1	1996-007979.NRAN.	DERWENT	OR	OFF	2005/02/08 13:05
S18	2	polishing same silicon adj carbide adj substrate and anneal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/08 13:10
S19	69	silicon adj carbide adj substrate and oxidizing adj atmosphere	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/08 14:25
S20	11	silicon adj carbide adj substrate same oxidizing adj atmosphere	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/08 13:11
S21	299	silicon adj carbide adj substrate and bonded	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/08 14:48
S22	441	silicon adj carbide adj substrate and epitaxial adj growth	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/08 15:11
S23	1	silicon adj carbide adj substrate and epitaxial adj growth and polishing and oxidizing adj atmosphere	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/08 15:38
S24	30	silicon adj carbide adj substrate and epitaxial adj growth and polishing and bonding	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/09 10:07
S25	4	silicon adj carbide adj substrate same bonding and epitaxial adj growth and polishing	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/09 10:29
S26	108	silicon adj carbide adj substrate and epitaxial adj growth and bonding	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/09 10:16

S27	3	silicon adj carbide adj substrate and epitaxial adj growth and bonding and RCA	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/09 10:18
S28	15	silicon adj carbide adj substrate same bonding and epitaxial adj growth	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/09 10:35
S29	66537	SiC silicon adj carbide and RCA SC1	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/17 13:33
S30	3854	silicon adj carbide and RCA SC1	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/17 13:36
S31	1214	silicon adj carbide and RCA SC1 and semiconductor	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/17 13:37
S32	1034	silicon adj carbide adj substrate and RCA SC1 and semiconductor	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/17 13:37
S33	1021	silicon adj carbide adj substrate same RCA SC1 and semiconductor	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/17 13:38
S34	0	silicon adj carbide adj substrate same RCA and polishing	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/17 13:39
S35	0	silicon adj carbide adj substrate same sc1 and polishing	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/17 13:39
S36	1	silicon adj carbide adj substrate same HF and polishing	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/17 13:40
S37	0	silicon adj carbide adj substrate same cleaning same polishing	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/17 13:41
S38	21	silicon adj carbide adj substrate same cleaning andpolishing	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/17 13:41

S39	1	silicon adj carbide adj substrate same cleaning and polishing	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/17 13:42
S40	6	silicon adj carbide adj substrate same clean and polishing	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/17 13:43
S41	6	silicon adj carbide adj substrate and (RCA or Hydroflouric) and polishing	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/17 19:29
S42	3	silicon adj carbide adj substrate and (RCA and Hydrofluoric) and polishing	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/17 19:29
S43	28140	colloidal adj silica	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 19:44
S44	1654	colloidal adj silica and silicon adj carbide	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/04 19:45
S45	2318	colloidal adj silica and silicon adj carbide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 19:46
S46	645	colloidal adj silica and silicon adj carbide and polishing	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 19:46
S47	143	colloidal adj silica and silicon adj carbide and polishing and "438"/$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 19:51
S48	15	colloidal adj silica and silicon adj carbide near5 (substrate or wafer) and polishing and "438"/$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 19:52
S49	18	colloidal adj silica and silicon adj carbide near5 (substrate or wafer) and polishing and ("438"/$.ccls. or "257"/$.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 14:24

S50	4	colloidal adj silica and silicon adj carbide adj (substrate or wafer) and polishing and ("438"/$.ccls. or "257"/$.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 14:39
S51	290	colloidal adj silica and surface adj roughness and ("438"/$.ccls. or "257"/$.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 14:40
S52	5	(("5877070") or ("6833562")).PN.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/05 15:57